

Features

- Frequency: 14GHz~18GHz
- Small Signal Gain: 20dB
- Output P_{-1dB}: 38 dBm
- PAE: 25%
- IM₃: -24dBc, 30dBm/Tone@16GHz
- Die Size: 3.4mm×3.57mm×0.1mm
- Supply Voltage: +8V/-V_g
- Packaged: Bare Die

General Description

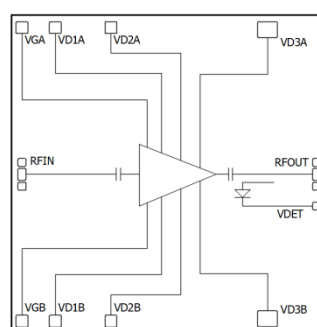
SAC3133B is a Ku-band GaAs MMIC power amplifier. SAC3133B provides 20 dB of gain, and 38dBm of output power for 1 dB compression and 25% PAE from +8V supply.

The chip has surface passivation for protection and backside via holes and gold metallization to allow a conductive epoxy die attach process.

Typical Applications

- Point-to-Point Radios
- SATCOM
- Military and Space
- Radar

Functional Diagram



Electrical Performance

T_A=25°C, V_D=+8V, I_{DQ}=2A, Z₀=50Ω, CW

Parameter	Min.	Typ.	Max.	Units
Frequency Range	14	—	18	GHz
Small Signal Gain	16	20	—	dB
Small Signal Gain Flatness	—	±1.5	—	dB
Reverse Isolation	—	-65	—	dB
RF Input Port Return Loss	—	-8	—	dB
Power Added Efficiency	—	25	—	%
Output P _{-1dB}	37	38	—	dBm
IM ₃ *	—	24	—	dBc
Drain Voltage (V _D)	—	8	—	V
Gate Current	—	2	22	mA
Supply Current (I _D)***	—	—	3.55	A
Thermal Resistance**	—	3.3	—	°C/W

* P_{out}/Tone= 30dBm, f_c = 16GHz, Δf = 4MHz

** Measurement taken at P_{out} = OP_{-1dB}

*** Adjust V_g between -1V to -0.6V to achieve I_{DQ}= 2A typical.

Absolute Maximum Ratings

Maximum Input Power	+23dBm	Operating Temperature (Backside)	-55°C~+85°C
Channel Temperature	165°C	Storage Temperature	-55°C~+150°C
Maximum V _D	+8.5V	V _G Range	-1.5V~-0.5V

SAC3133B



GaAs MMIC Power Amplifier
14GHz~18GHz 38dBm

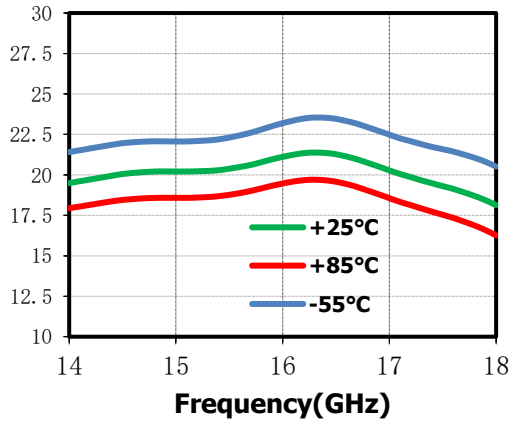
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Typical Performance Curve

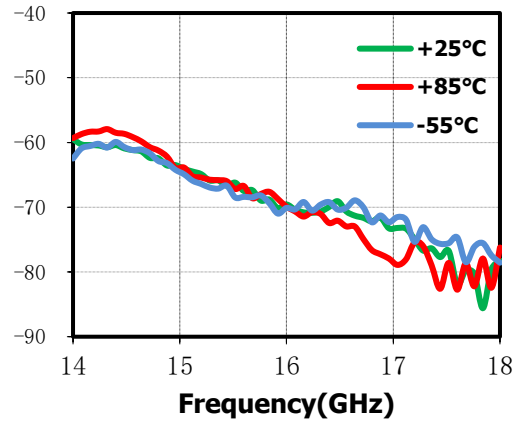
The following data are obtained by SAC3133B evaluation board

$V_D = +8V, I_{DQ} = 2A, CW, T_A = +25^\circ C$

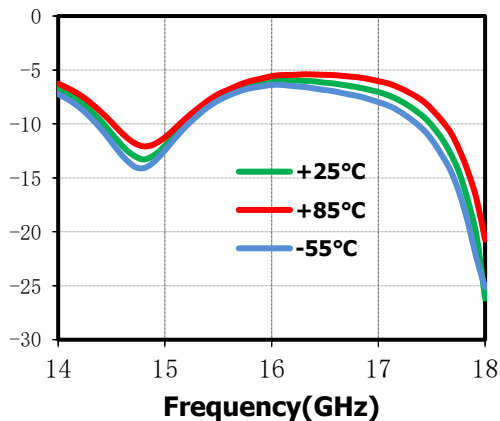
Small Signal Gain(dB) vs. Temperature



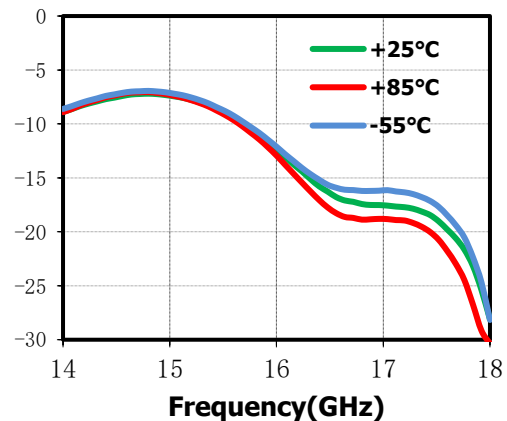
Isolation(dB) vs. Temperature



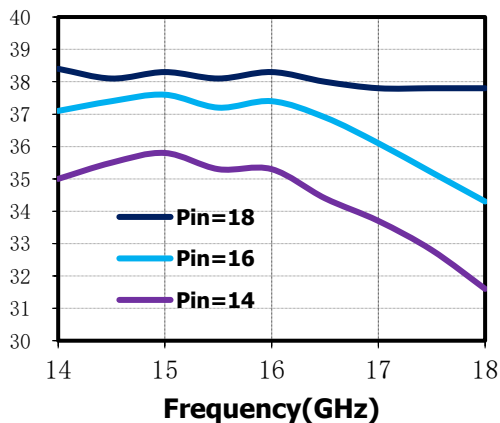
Input RL(dB) vs. Temperature



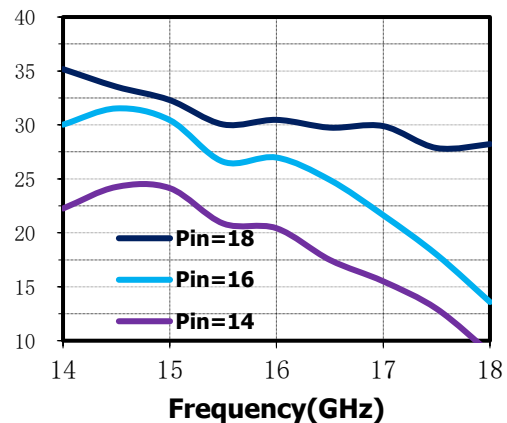
Output RL(dB) vs. Temperature



Pout(dBm) vs. Pin(dBm), $T_A = +25^\circ C$



PAE(%) vs. Pin(dBm), $T_A = +25^\circ C$



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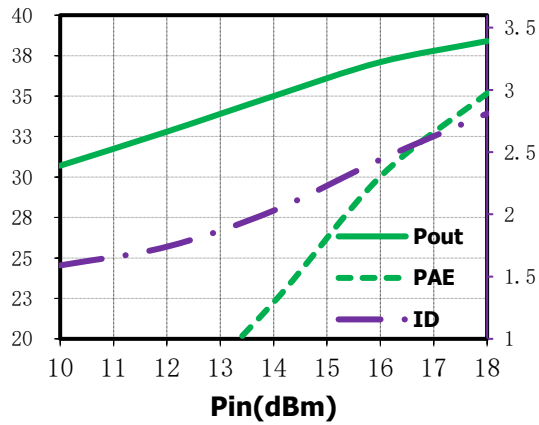
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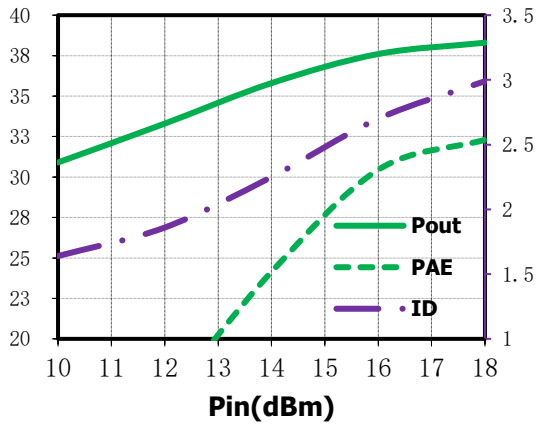
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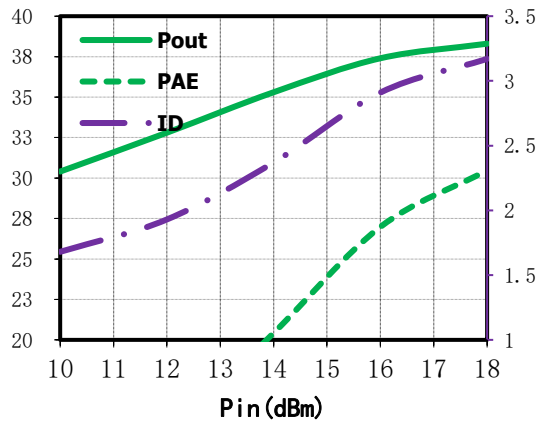
Pout(dBm), PAE(%), ID(A) vs. Pin,f=14GHz



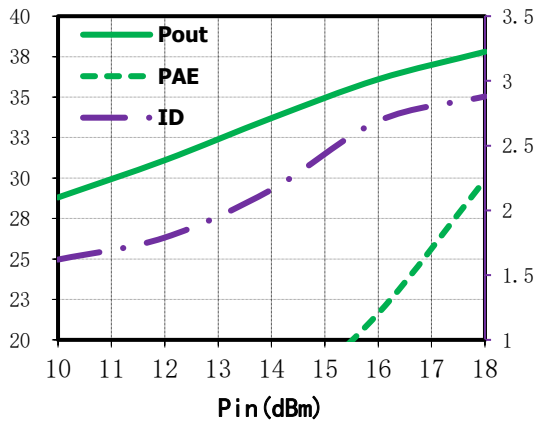
Pout(dBm), PAE(%), ID(A) vs. Pin,f=15GHz



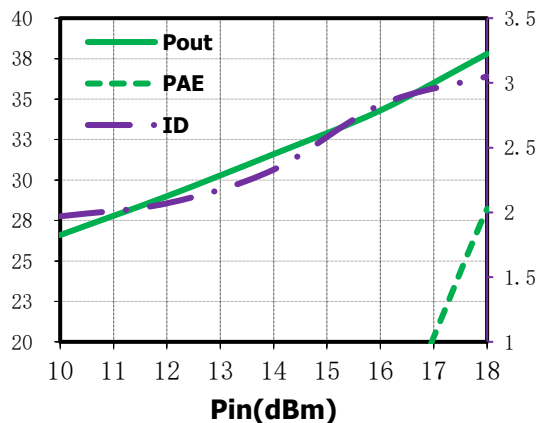
Pout(dBm), PAE(%), ID(A) vs. Pin,f=16GHz



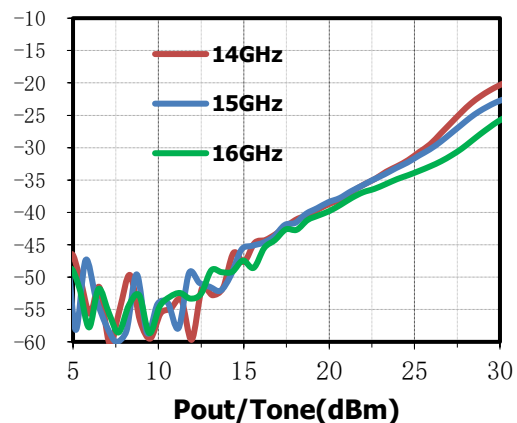
Pout(dBm), PAE(%), ID(A) vs. Pin,f=17GHz



Pout(dBm), PAE(%), ID(A) vs. Pin,f=18GHz



IM3(dBc) vs. Pout/Tone



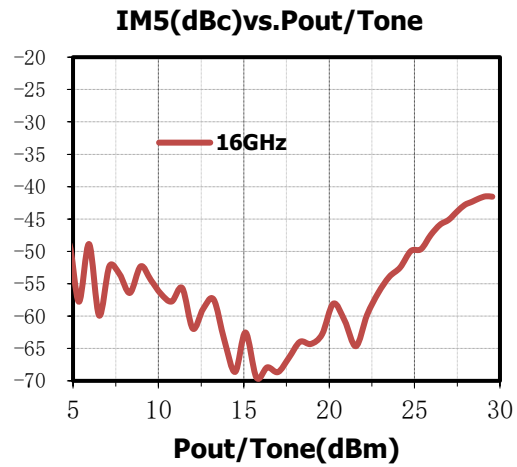
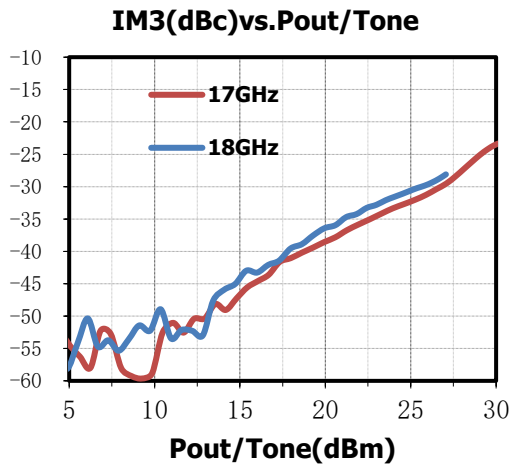
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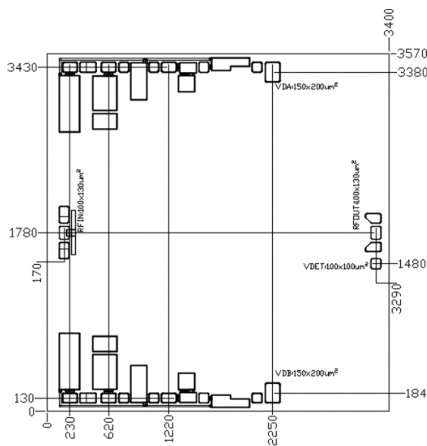
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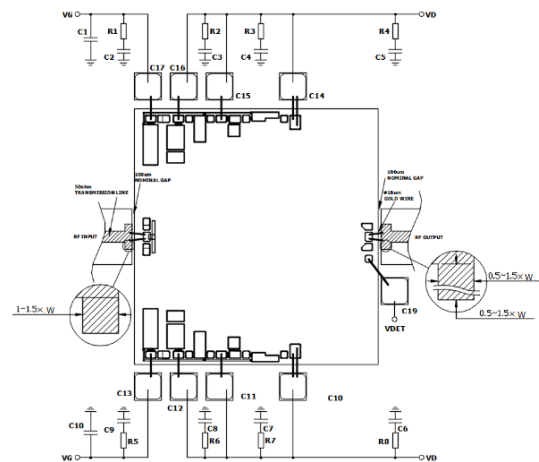
Die Outline

(All dimensions in μm)



Pads size: $100 \times 130 \mu\text{m}^2$, $t=100 \mu\text{m}$

Assembly Diagram



Components List

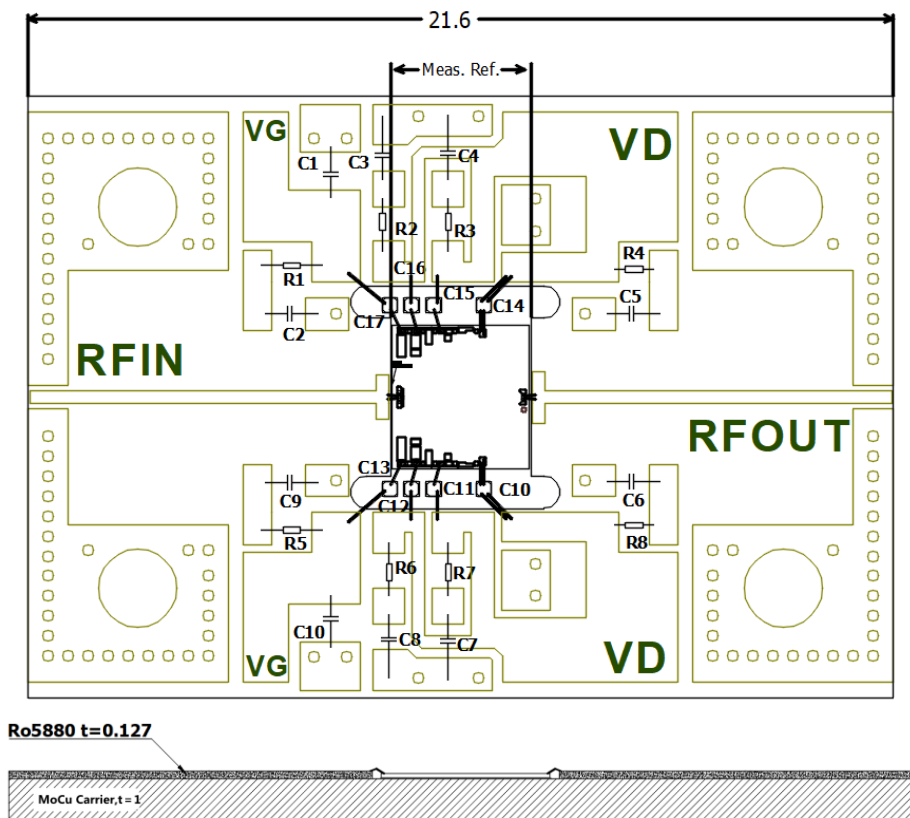
Reference Des.	Value	Part Number	Manuf.	Size
C10~C17, C19	100pF	—	—	SLC
C2~C9	0.47 μF	—	—	0603
C1, C10	10 μF	—	—	0805
R1~R8	1 Ω	—	—	0603

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SAC3133B EVB



Attention:

1. SAC3133B is biased with a positive drain supply and negative gate supply. The recommended gate voltage is set to -0.6 to -1V when the drain voltage is set to 8V;
2. RF connections should be made as short as possible to reduce the inductive effect of the bond wire. Use of a 0.8 mil thermosonic wedge bonding is highly recommended as the loop height will be minimized;
3. Vacuum AuSn eutectic soldering is recommended;
4. The maximum spike voltage at drains (VDxx) should not exceed 8.5v.

Revision History

Revision	Date	Comment
1.0	Apr. 15, 2022	First Release

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